

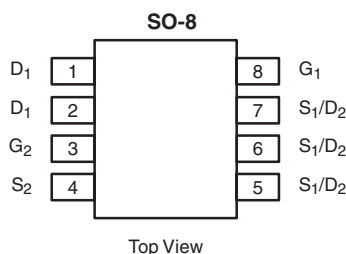
Dual N-Channel 30-V (D-S) MOSFET with Schottky Diode

PRODUCT SUMMARY

	V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A) ^a	Q _g (Typ.)
Channel-1	30	0.016 at V _{GS} = 10 V	10.7	8
		0.024 at V _{GS} = 4.5 V	8.6	
Channel-2	30	0.015 at V _{GS} = 10 V	11.3	19
		0.017 at V _{GS} = 4.5 V	10.6	

SCHOTTKY PRODUCT SUMMARY

V _{DS} (V)	V _{SD} (V) Diode Forward Voltage	I _F (A)
30	0.43 V at 2.0 A	2.0



Ordering Information: Si4388DY-T1-E3 (Lead (Pb)-free)
Si4388DY-T1-GE3 (Lead (Pb)-free and Halogen-free)

FEATURES

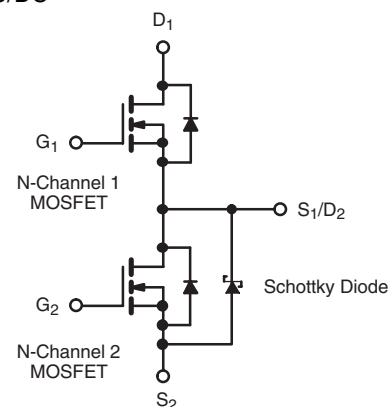
- Halogen-free According to IEC 61249-2-21 Available
- TrenchFET® Power MOSFET
- 100 % R_g and UIS Tested

APPLICATIONS

- CCFL Inverter
- Notebook Logic DC/DC



RoHS
COMPLIANT
HALOGEN
FREE
Available



ABSOLUTE MAXIMUM RATINGS T_A = 25 °C, unless otherwise noted

Parameter		Symbol	Channel-1	Channel-2	Unit
Drain-Source Voltage		V _{DS}	30	30	V
Gate-Source Voltage		V _{GS}	± 20	± 12	
Continuous Drain Current (T _J = 150 °C)	T _C = 25 °C	I _D	10.7	11.3	A
	T _C = 70 °C		8.5	- 9	
	T _A = 25 °C		8.1 ^{b, c}	8.6 ^{b, c}	
	T _A = 70 °C		6.4 ^{b, c}	6.9 ^{b, c}	
Pulsed Drain Current (10 μs Pulse Width)		I _{DM}	40	40	
Source-Drain Current Diode Current	T _C = 25 °C	I _S	3.0	3.2	
	T _A = 25 °C		1.7 ^{b, c}	1.8 ^{b, c}	
Pulsed Source-Drain Current		I _{SM}	40	40	mJ
Single Pulse Avalanche Current		I _{AS}	15	20	
Single Pulse Avalanche Energy		E _{AS}	11.2	20	
Maximum Power Dissipation	T _C = 25 °C	P _D	3.3	3.5	W
	T _C = 70 °C		2.1	2.2	
	T _A = 25 °C		1.9 ^{b, c}	2.2 ^{b, c}	
	T _A = 70 °C		1.2 ^{b, c}	1.3 ^{b, c}	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150		°C

THERMAL RESISTANCE RATINGS

Parameter		Symbol	Channel-1		Channel-2		Unit
			Typ.	Max.	Typ.	Max.	
Maximum Junction-to-Ambient ^{b, d}	t ≤ 10 s	R _{thJA}	54	65	47	60	°C/W
Maximum Junction-to-Foot (Drain)	Steady State	R _{thJF}	32	38	30	35	

Notes:

a. Based on T_C = 25 °C.

b. Surface Mounted on 1" x 1" FR4 board.

c. t = 10 s.

d. Maximum under Steady State conditions is 112 °C/W (Channel-1) and 107 °C/W (Channel-2).

SPECIFICATIONS $T_J = 25\text{ }^{\circ}\text{C}$, unless otherwise noted

Parameter	Symbol	Test Conditions		Min.	Typ. ^a	Max.	Unit
Static							
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA	Ch-1	30			V
		V _{GS} = 0 V, I _D = 1 mA	Ch-2	30			
V _{DS} Temperature Coefficient	ΔV _{DS} /T _J	I _D = 250 μA	Ch-1		27		
V _{GS(th)} Temperature Coefficient	ΔV _{GS(th)} /T _J	I _D = 250 μA	Ch-1		- 6		
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	Ch-1	1		3	
		V _{DS} = V _{GS} , I _D = 1 mA	Ch-2	0.6		1.6	
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V	Ch-1			100	μA
		V _{DS} = 0 V, V _{GS} = ± 12 V	Ch-2			100	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 30 V, V _{GS} = 0 V	Ch-1			0.001	mA
		V _{DS} = 30 V, V _{GS} = 0 V	Ch-2		0.22	1	
		V _{DS} = 30 V, V _{GS} = 0 V, T _J = 100 °C	Ch-1			0.025	
		V _{DS} = 30 V, V _{GS} = 0 V, T _J = 100 °C	Ch-2		12	100	
On-State Drain Current ^b	I _{D(on)}	V _{DS} = 5 V, V _{GS} = 10 V	Ch-1	20			A
		V _{DS} = 5 V, V _{GS} = 10 V	Ch-2	20			
Drain-Source On-State Resistance ^b	R _{DS(on)}	V _{GS} = 10 V, I _D = 8 A	Ch-1		0.013	0.016	Ω
		V _{GS} = 10 V, I _D = 8 A	Ch-2		0.0125	0.015	
		V _{GS} = 4.5 V, I _D = 5 A	Ch-1		0.017	0.024	
		V _{GS} = 5 V, I _D = 5 A	Ch-2		0.014	0.017	
Forward Transconductance ^b	g _{fs}	V _{DS} = 15 V, I _D = 8 A	Ch-1		20		S
		V _{DS} = 15 V, I _D = 8 A	Ch-2		38		
Dynamic ^a							
Input Capacitance	C _{iss}	Channel-1 V _{DS} = 15 V, V _{GS} = 0 V, f = 1 MHz	Ch-1		946		pF
			Ch-2		2230		
Output Capacitance	C _{oss}	Channel-2 V _{DS} = 15 V, V _{GS} = 0 V, f = 1 MHz	Ch-1		173		
			Ch-2		350		
Reverse Transfer Capacitance	C _{rss}		Ch-1		84		
			Ch-2		133		
Total Gate Charge	Q _g	V _{DS} = 15 V, V _{GS} = 10 V, I _D = 5 A	Ch-1		18	27	nC
		V _{DS} = 15 V, V _{GS} = 10 V, I _D = 5 A	Ch-2		41	62	
		Channel-1 V _{DS} = 15 V, V _{GS} = 4.5 V, I _D = 5 A	Ch-1		8	12	
			Ch-2		19	29	
Gate-Source Charge	Q _{gs}	Channel-2 V _{DS} = 15 V, V _{GS} = 4.5 V, I _D = 5 A	Ch-1		2.55		
			Ch-2		3.5		
Gate-Drain Charge	Q _{gd}		Ch-1		2.45		
			Ch-2		3.7		
Gate Resistance	R _g	f = 1 MHz	Ch-1		2.8	4.2	Ω
			Ch-2		1.8	2.7	



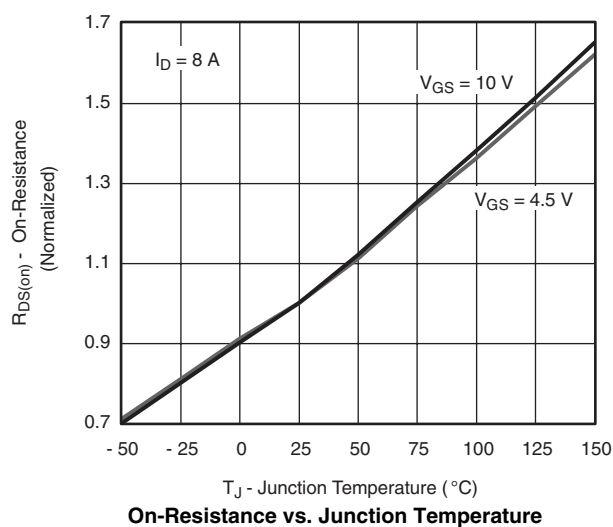
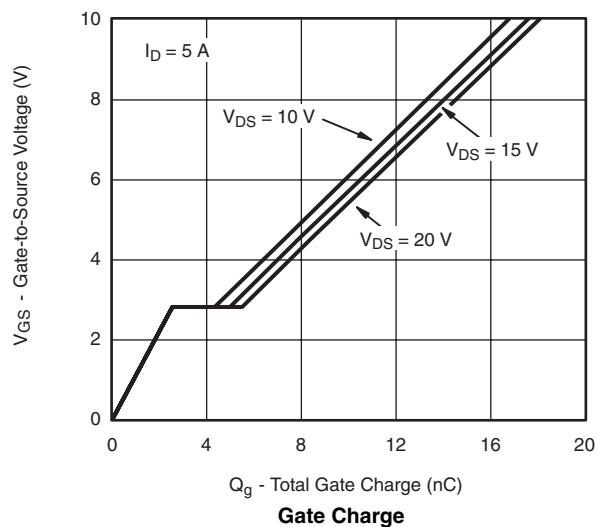
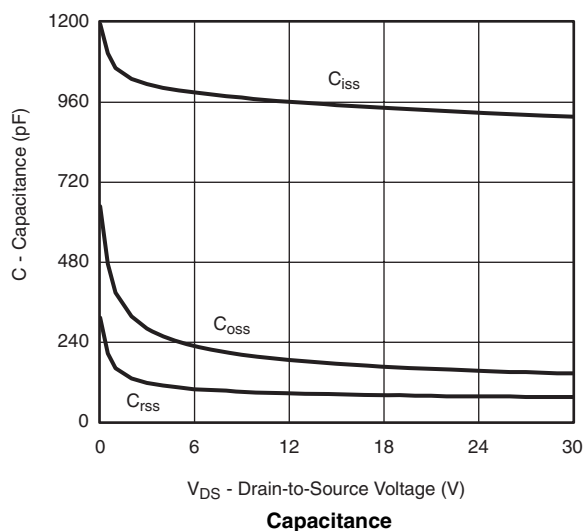
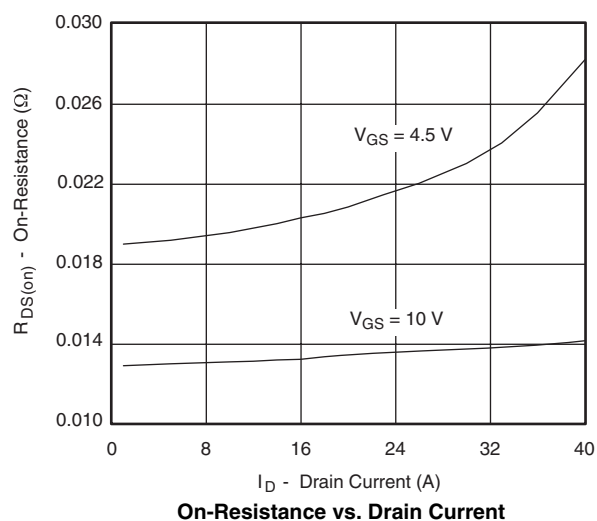
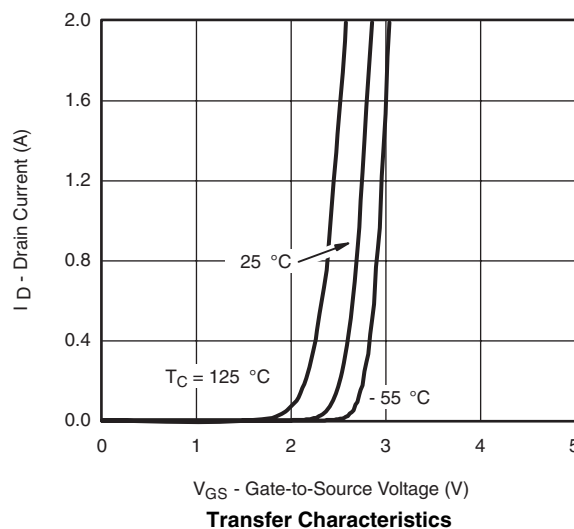
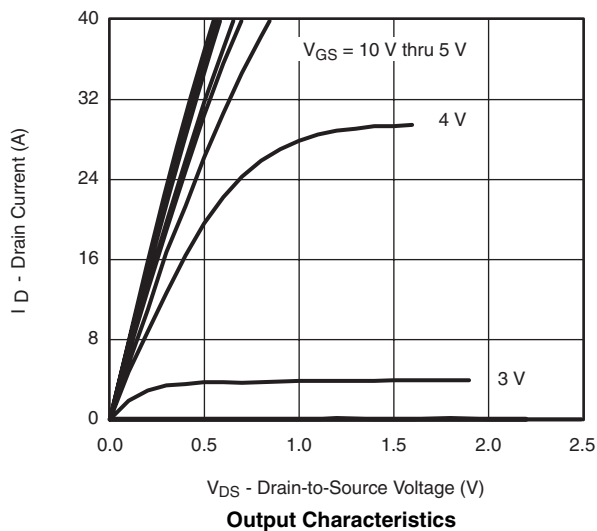
SPECIFICATIONS T _J = 25 °C, unless otherwise noted							
Parameter	Symbol	Test Conditions		Min.	Typ. ^a	Max.	Unit
Dynamic ^a							
Turn-On Delay Time	t _{d(on)}	Channel-1 V _{DD} = 15 V, R _L = 3 Ω I _D ≅ 5 A, V _{GEN} = 10 V, R _g = 1 Ω	Ch-1		8	15	ns
			Ch-2		7	14	
Rise Time	t _r		Ch-1		10	15	
			Ch-2		10	15	
Turn-Off Delay Time	t _{d(off)}	Ch-1		20	30		
		Ch-2		40	60		
Fall Time	t _f	Ch-1		8	15		
		Ch-2		7	14		
Turn-On Delay Time	t _{d(on)}	Channel-1 V _{DD} = 15 V, R _L = 3 Ω I _D ≅ 5 A, V _{GEN} = 4.5 V, R _g = 1 Ω	Ch-1		13	20	
			Ch-2		14	22	
Rise Time	t _r		Ch-1		17	26	
			Ch-2		15	24	
Turn-Off Delay Time	t _{d(off)}	Ch-1		16	25		
		Ch-2		35	53		
Fall Time	t _f	Ch-1		8	15		
		Ch-2		7	14		
Drain-Source Body Diode Characteristics							
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C	Ch-1			3	A
			Ch-2			3.2	
Pulse Diode Forward Current ^a	I _{SM}		Ch-1			40	
			Ch-2			40	
Body Diode Voltage	V _{SD}	I _S = 2 A	Ch-1		0.8	1.1	V
		I _S = 2 A	Ch-2		0.37	0.43	
Body Diode Reverse Recovery Time	t _{rr}	Channel-1 I _F = 1.3 A, dI/dt = 100 A/μs, T _J = 25 °C	Ch-1		29	44	ns
			Ch-2		32	48	
Body Diode Reverse Recovery Charge	Q _{rr}		Ch-1		19	29	nC
			Ch-2		21	32	
Reverse Recovery Fall Time	t _a	Channel-2 I _F = 2.2 A, dI/dt = 100 A/μs, T _J = 25 °C	Ch-1		12		ns
			Ch-2		13		
Reverse Recovery Rise Time	t _b		Ch-1		17		
			Ch-2		19		

Notes:

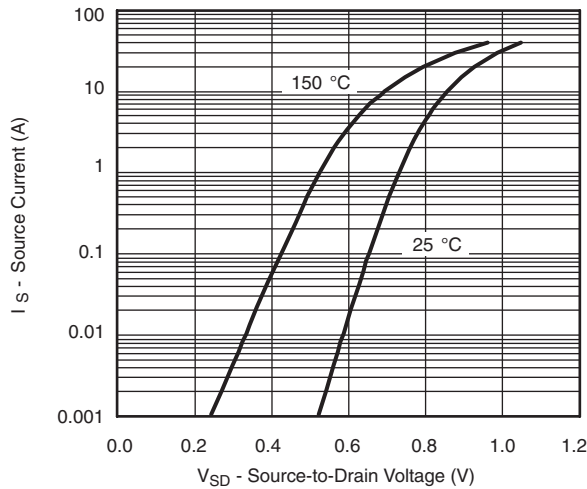
a. Guaranteed by design, not subject to production testing.

b. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\text{ }\%$.

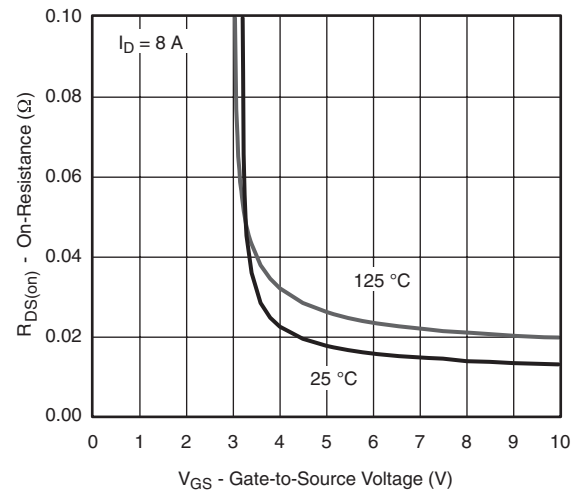
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

CHANNEL-1 TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

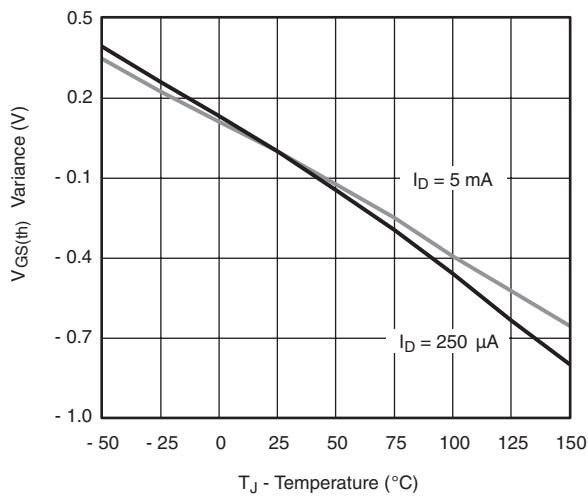
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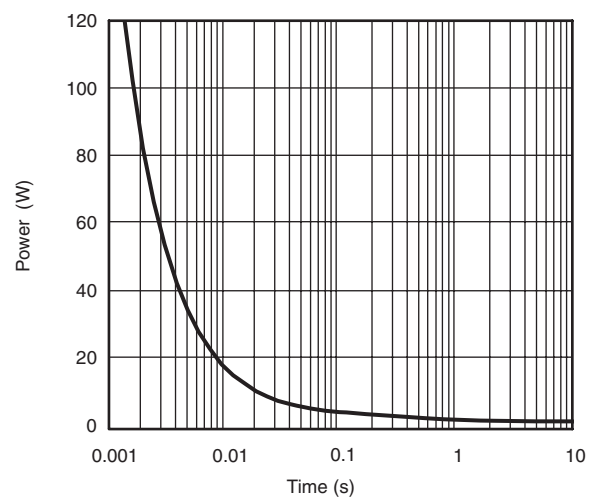
Source-Drain Diode Forward Voltage



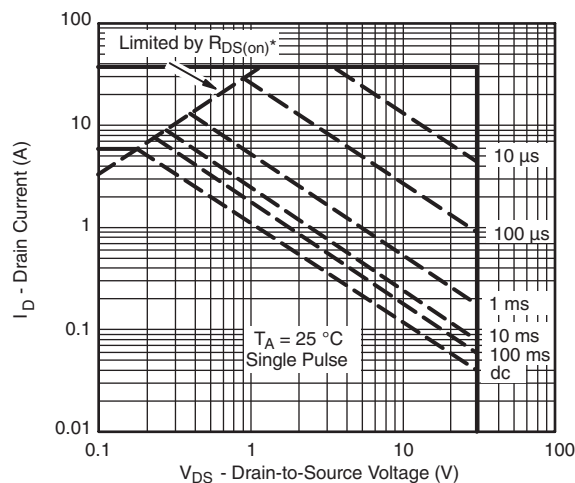
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage

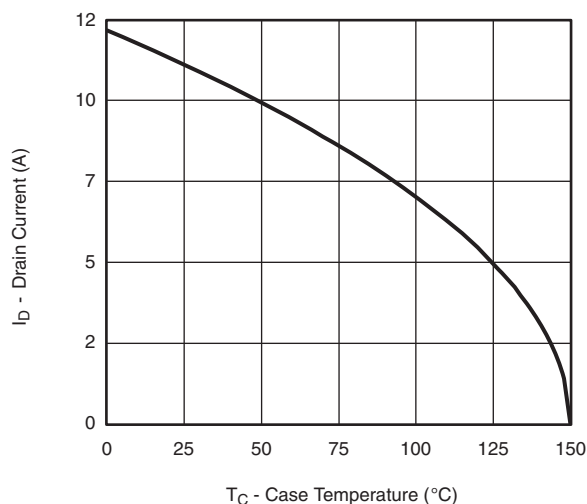
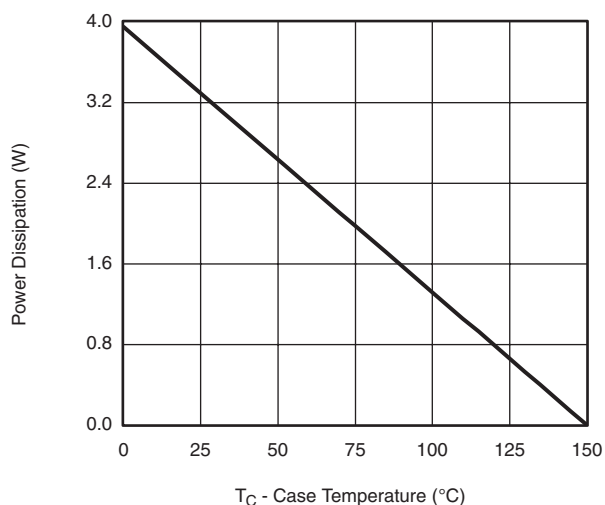
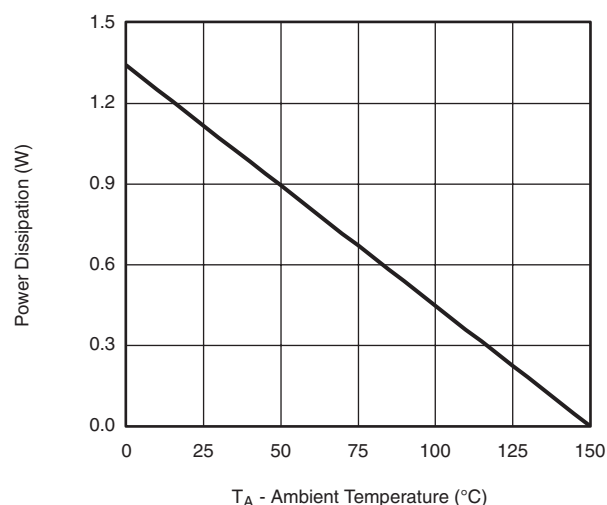


Single Pulse Power, Junction-to-Ambient



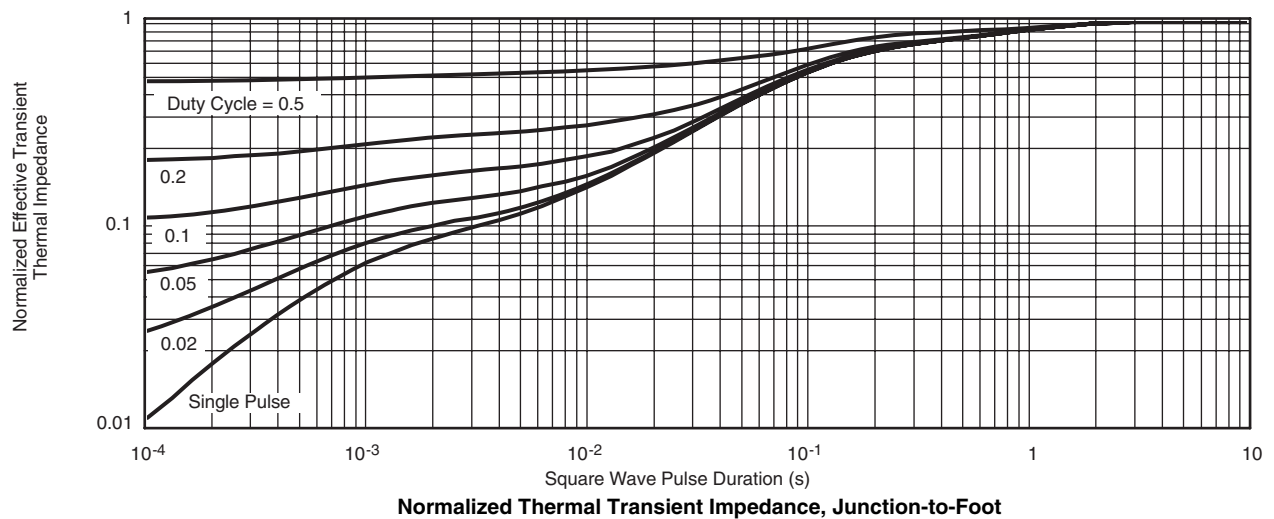
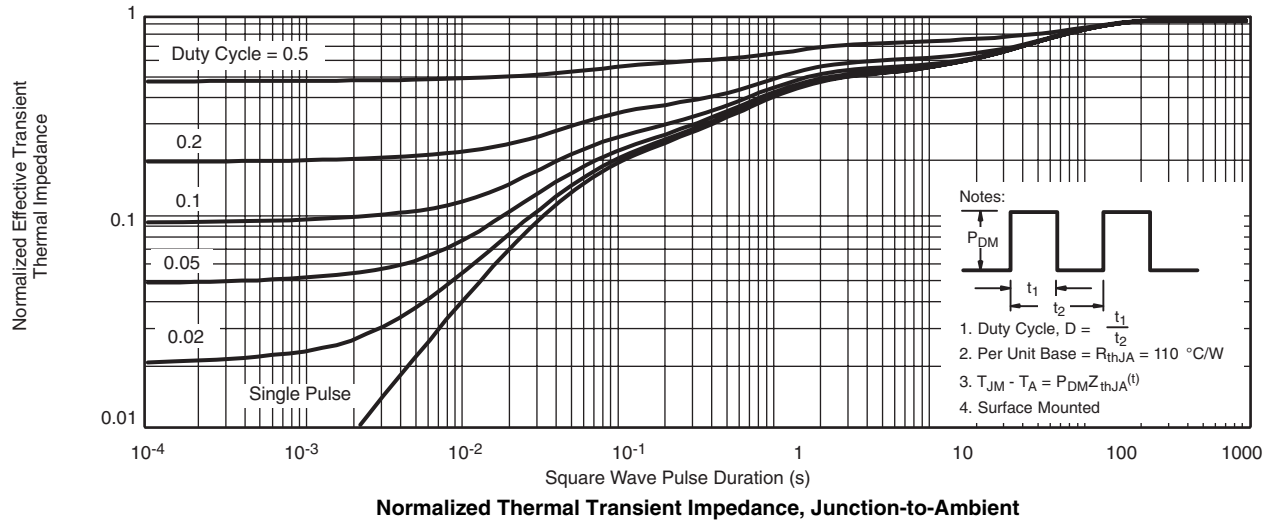
* V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

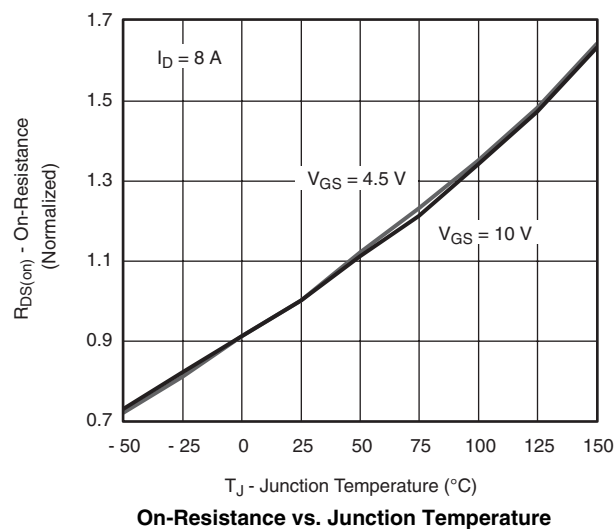
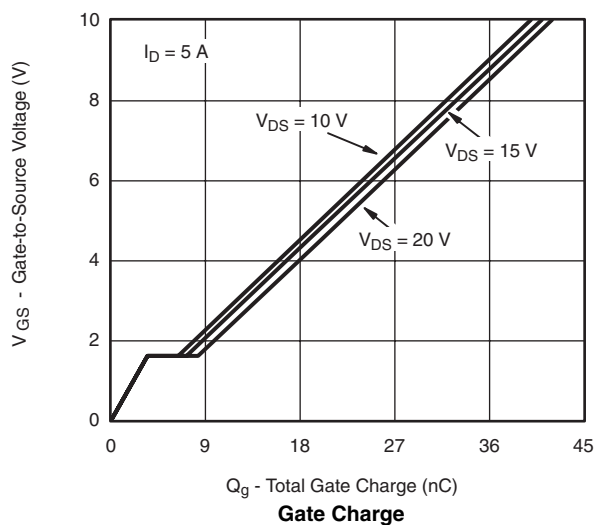
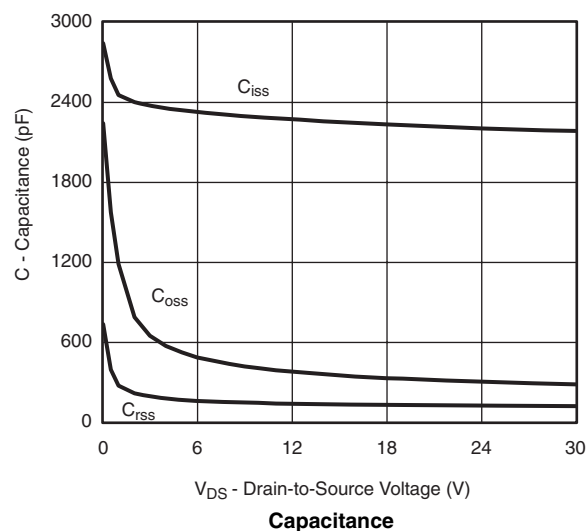
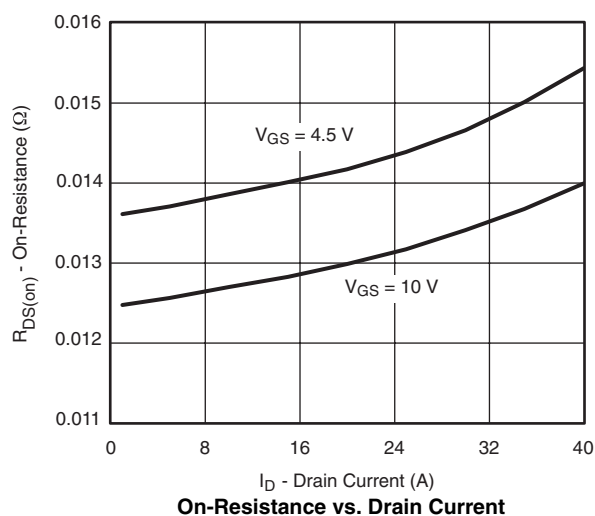
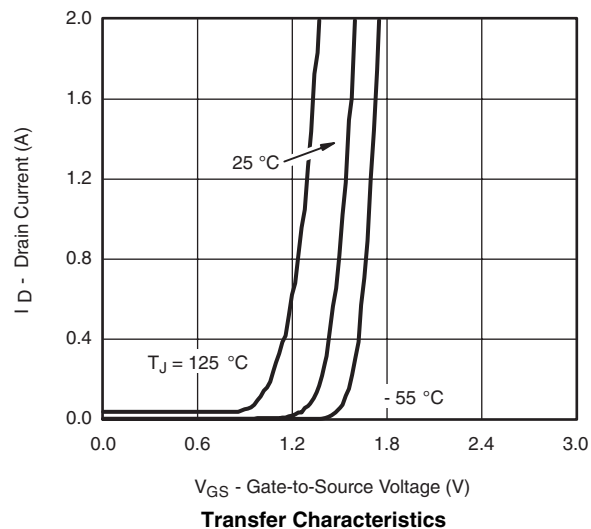
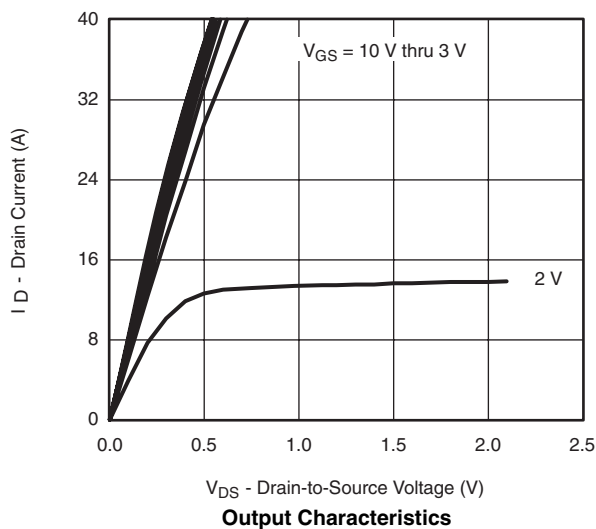
Safe Operating Area, Junction-to-Ambient

CHANNEL-1 TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted**Current Derating*****Power Derating, Junction-to-Foot****Power Derating, Junction-to-Ambient**

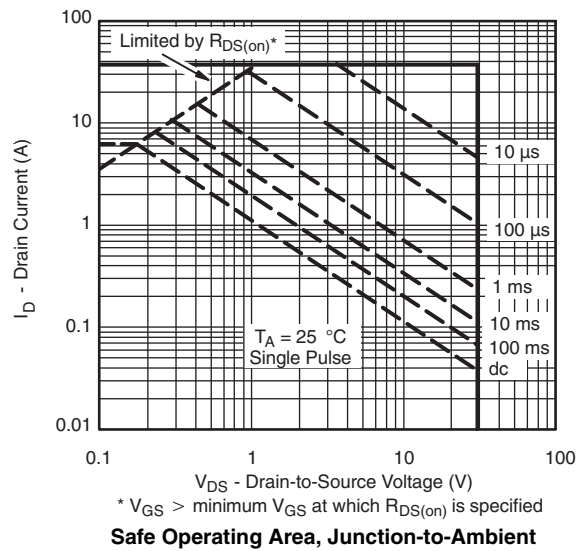
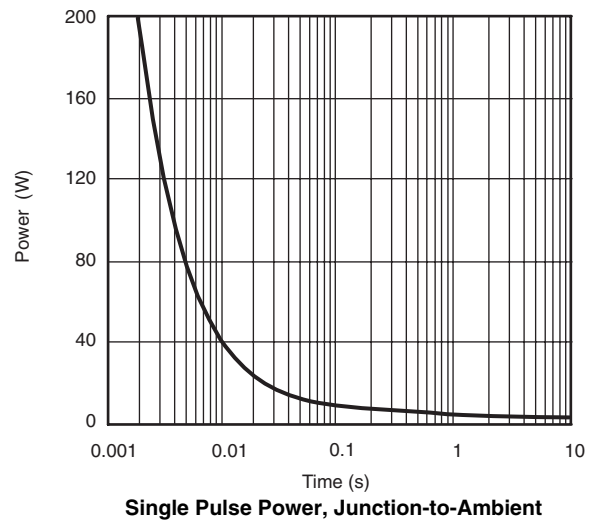
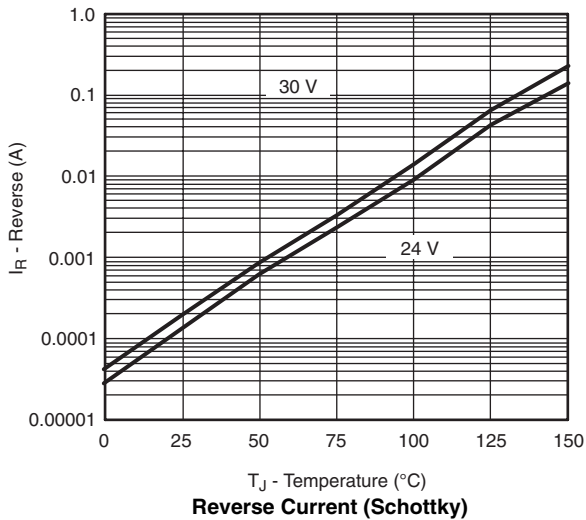
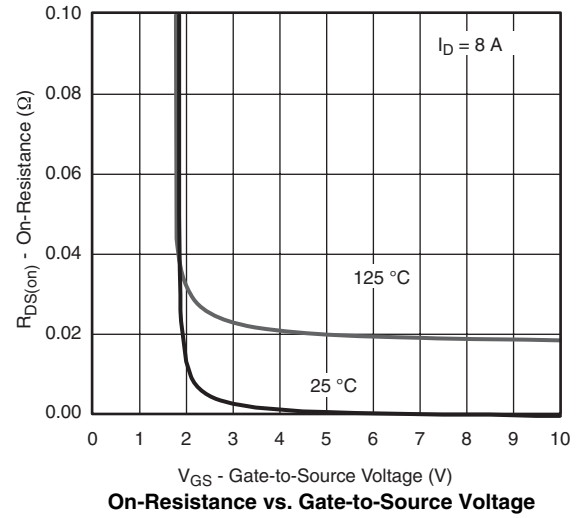
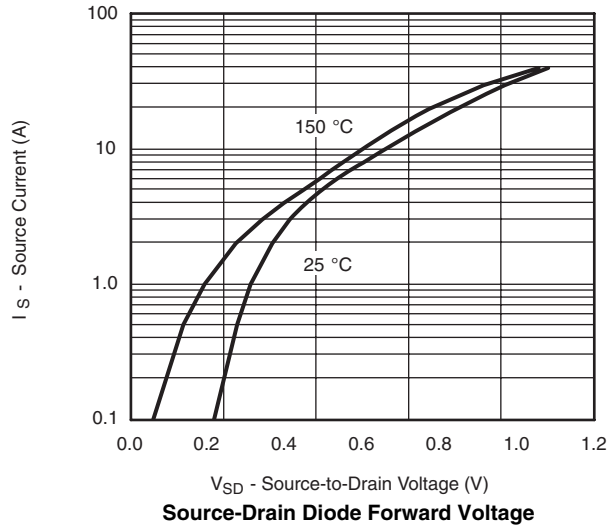
* The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

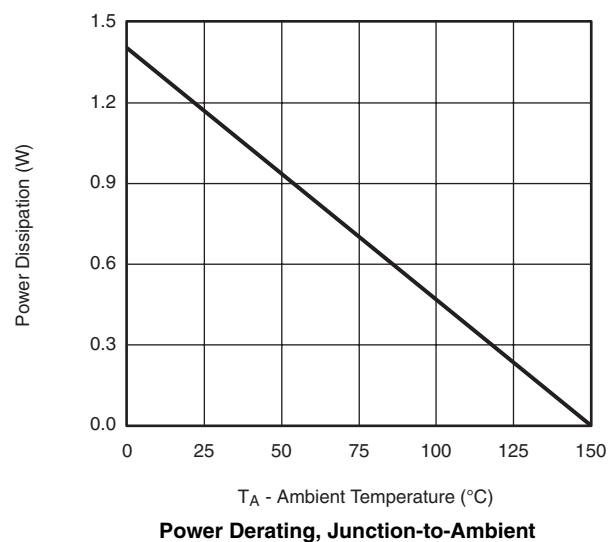
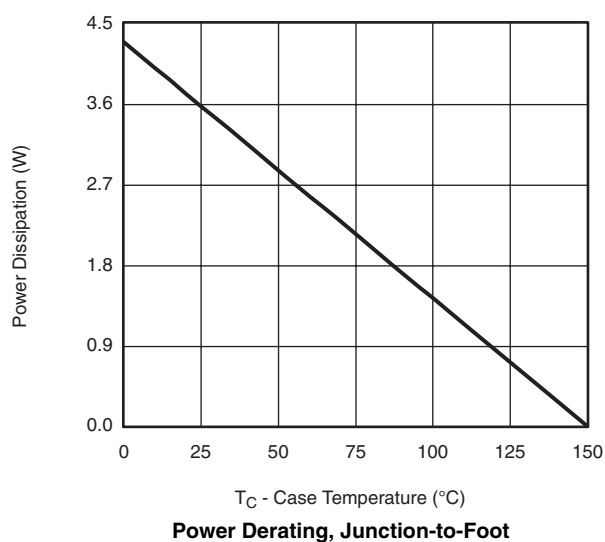
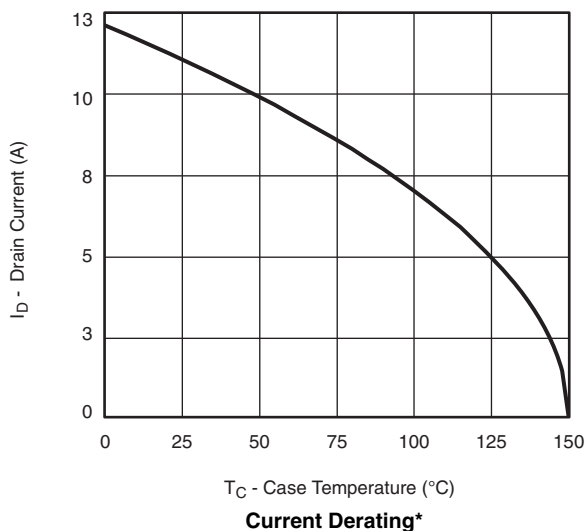
CHANNEL-1 TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



CHANNEL-2 TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

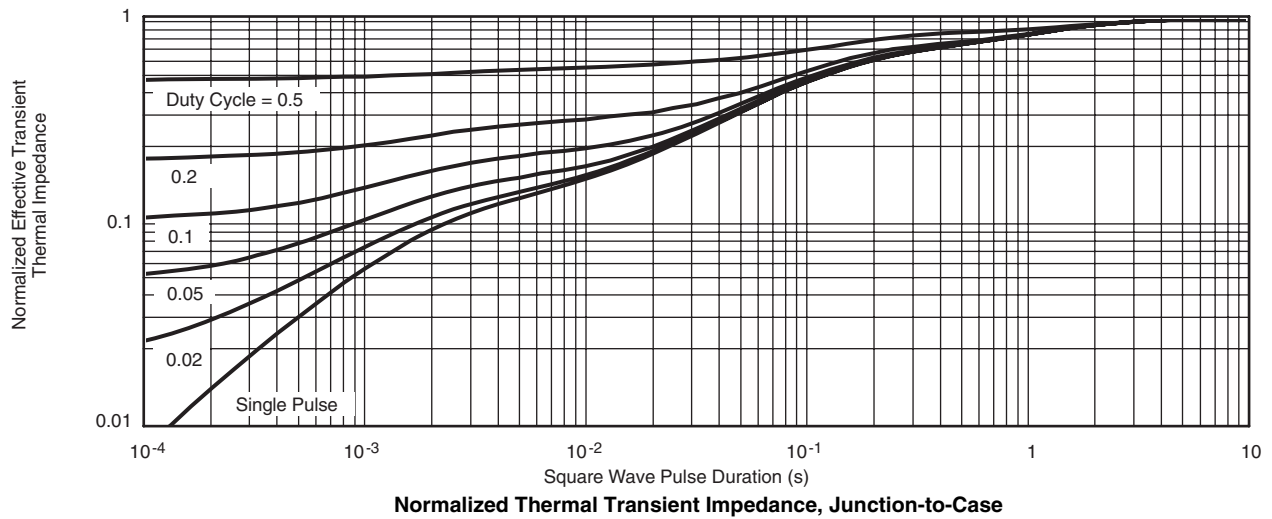
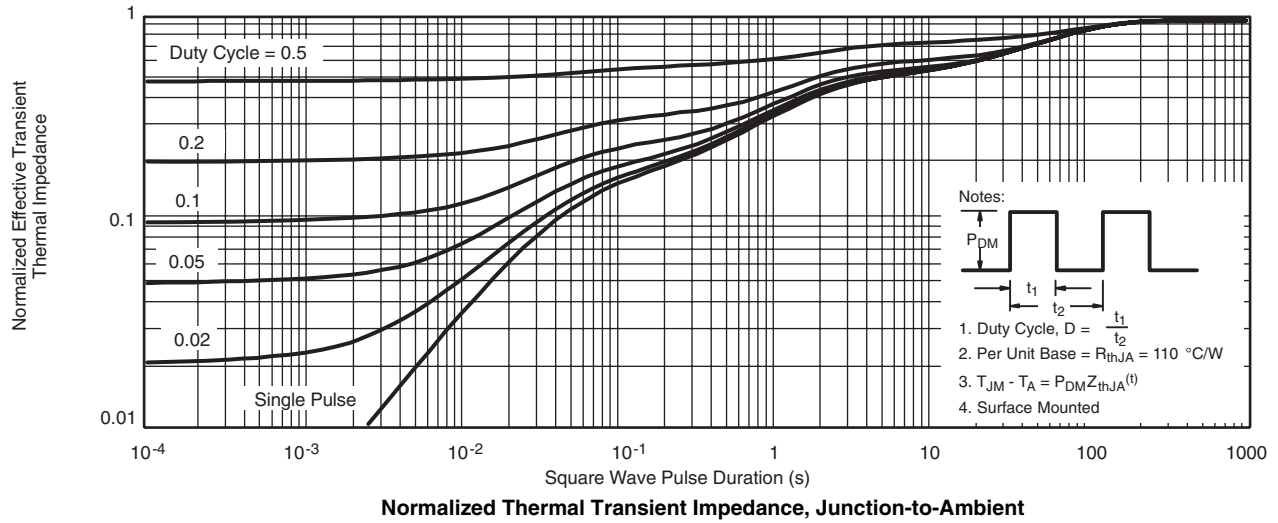
CHANNEL-2 TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



CHANNEL-2 TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

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CHANNEL-2 TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



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